THE DATASHEET OF

DMN6040SSS-13

www.win-source.net 0086-755-83957316

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = 25°C$
60V	40mΩ @ V_{GS} = 10V	5.5A
	55mΩ @ V_{GS} = 4.5V	4.7A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Description and Applications

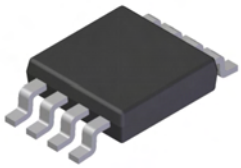
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

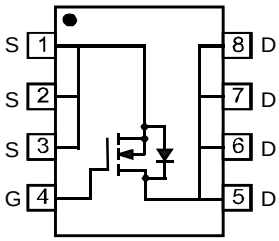
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.008 grams (approximate)

SO-8



Top View



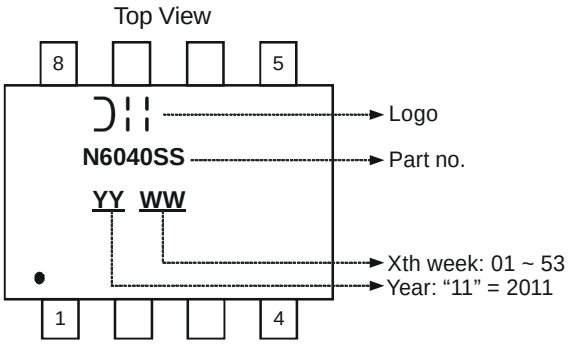
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6040SSS-13	SO-8	2500/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



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Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = 25°C T_A = 70°C	I_D	5.5 4.4	A
	t<10s	T_A = 25°C T_A = 70°C	I_D	7.0 5.5	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	2.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	30	A
Avalanche Current (Note 7) L = 0.1mH			I_{AR}	14.2	A
Repetitive Avalanche Energy (Note 7) L = 0.1mH			E_{AR}	10	mJ

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = 25°C	P_D	1.5	W
	T_A = 70°C		1	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	80	°C/W
	t<10s		48	
Total Power Dissipation (Note 6)	T_A = 25°C	P_D	2.0	W
	T_A = 70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	61	°C/W
	t<10s		37	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	6.4	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Electrical Characteristics T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	100	nA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	30	40	mΩ	V_{GS} = 10V, I_D = 4.5A
		—	35	55		V_{GS} = 4.5V, I_D = 3.5A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	4.5	—	S	V_{DS} = 10V, I_D = 4.3A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1287	—	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	57	—		
Reverse Transfer Capacitance	C_{rss}	—	44	—		
Gate Resistance	R_G	—	1.2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	22.4	—	nC	V_{DS} = 30V, I_D = 4.3A
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	10.4	—		
Gate-Source Charge	Q_{gs}	—	4.9	—		
Gate-Drain Charge	Q_{gd}	—	3.0	—		
Turn-On Delay Time	$t_{D(on)}$	—	6.6	—	nS	V_{GS} = 10V, V_{DD} = 30V, R_G = 6Ω, I_D = 4.3A
Turn-On Rise Time	t_r	—	8.1	—		
Turn-Off Delay Time	$t_{D(off)}$	—	20.1	—		
Turn-Off Fall Time	t_f	—	4.0	—		
Body Diode Reverse Recovery Time	t_{rr}	—	18	—	nS	I_S = 4.3A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{rr}	—	11.9	—	nC	I_S = 4.3A, dI/dt = 100A/µs

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = 25°C
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

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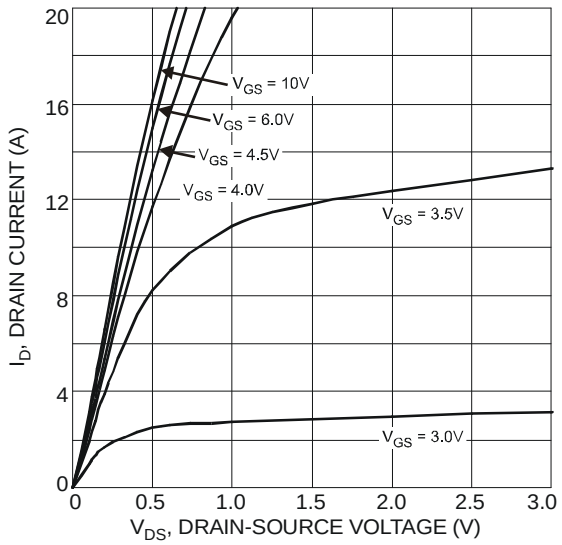

Fig.1 Typical Output Characteristic

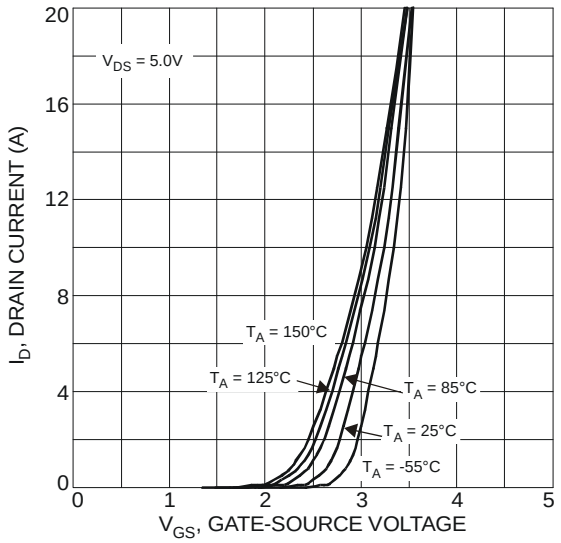

Fig.2 Typical Transfer Characteristics

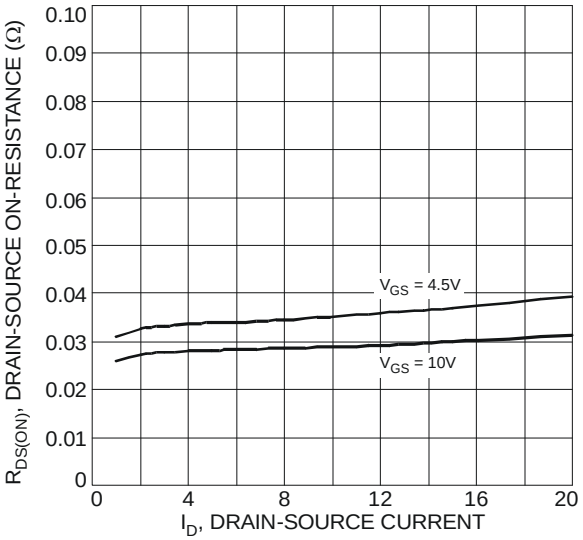

Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

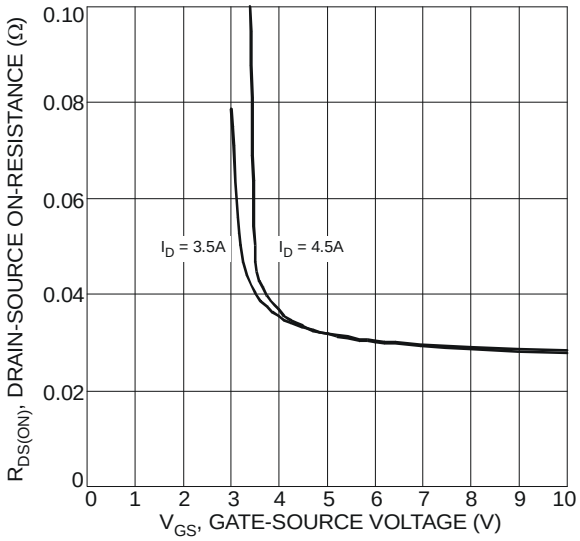

Fig. 4 Typical On-Resistance vs. Drain Current and Gate Voltage

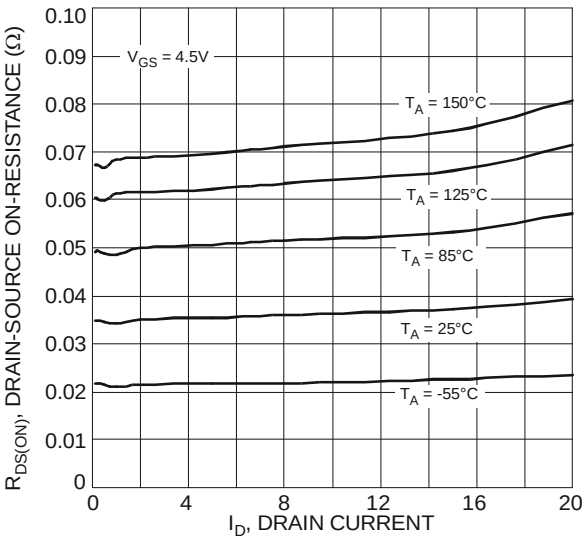

Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

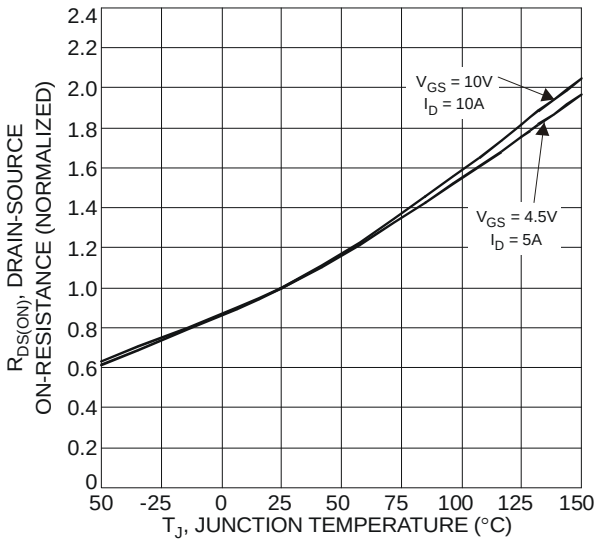

Fig. 6 On-Resistance Variation with Temperature

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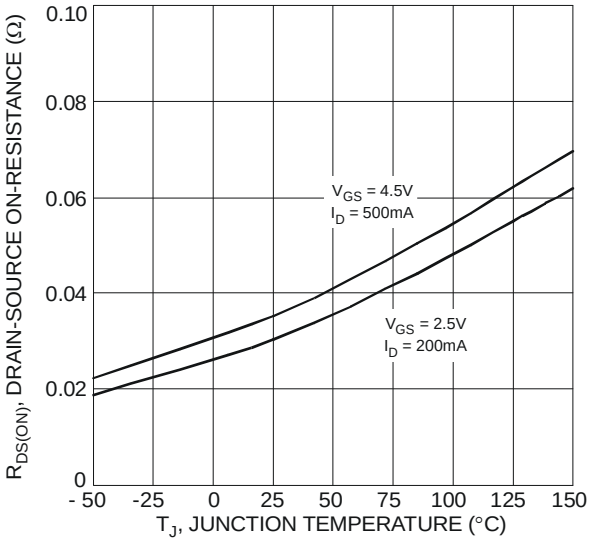

Fig. 7 On-Resistance Variation with Temperature

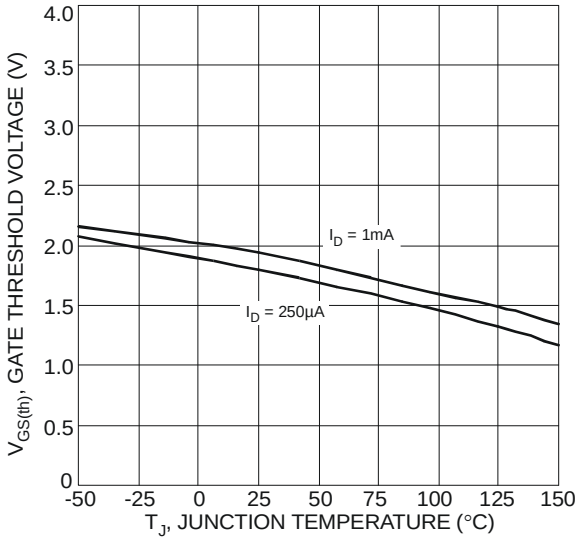

Fig. 8 Gate Threshold Variation vs. Ambient Temperature

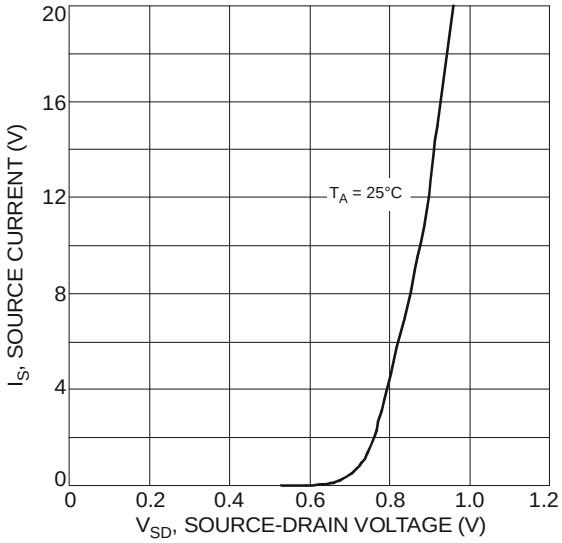

Fig.9 Diode Forward Voltage vs. Current

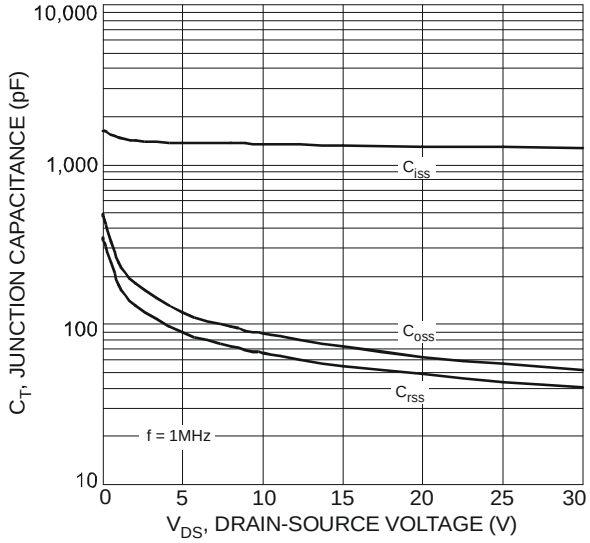

Fig. 10 Typical Junction Capacitance

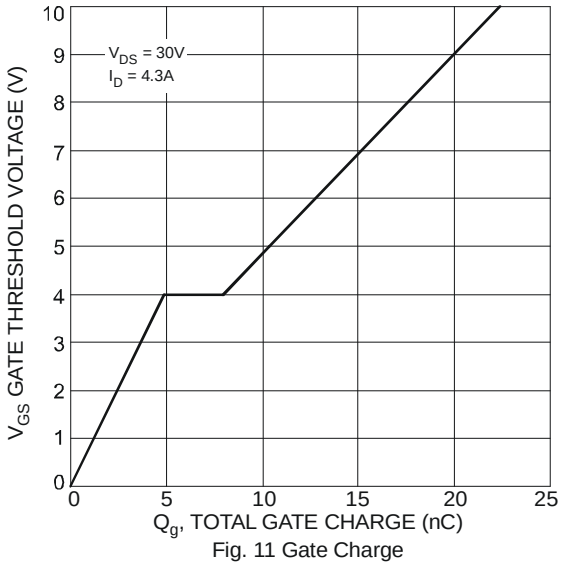

Fig. 11 Gate Charge

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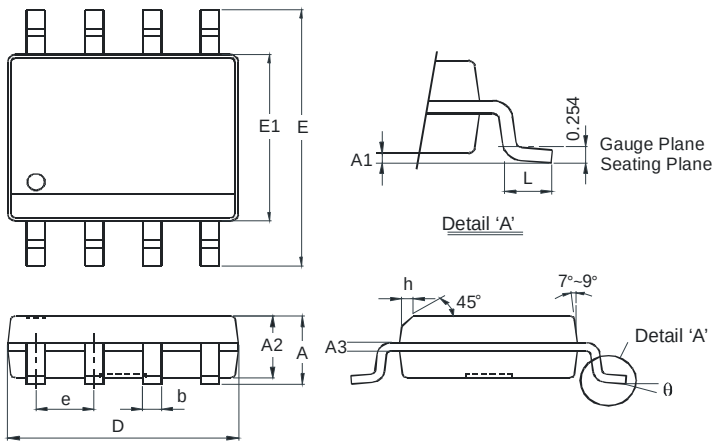
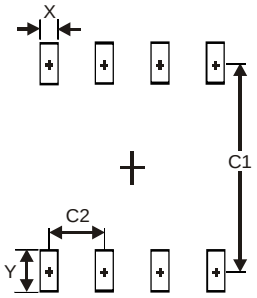
Package Outline Dimensions



SO-8		
Dim	**Min**	**Max**
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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